

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

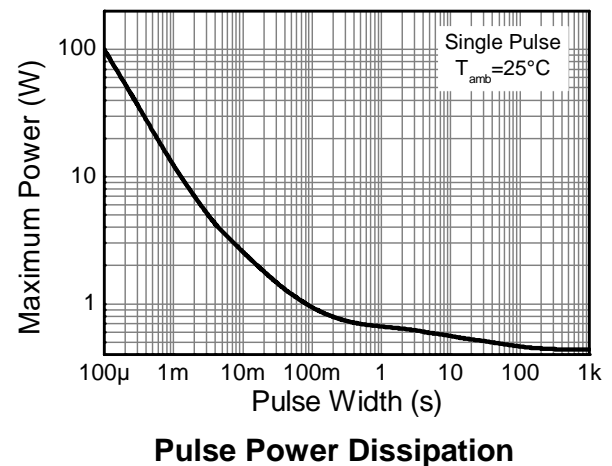
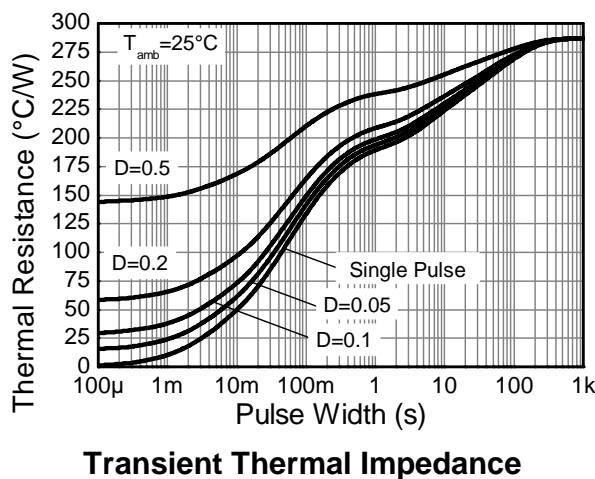
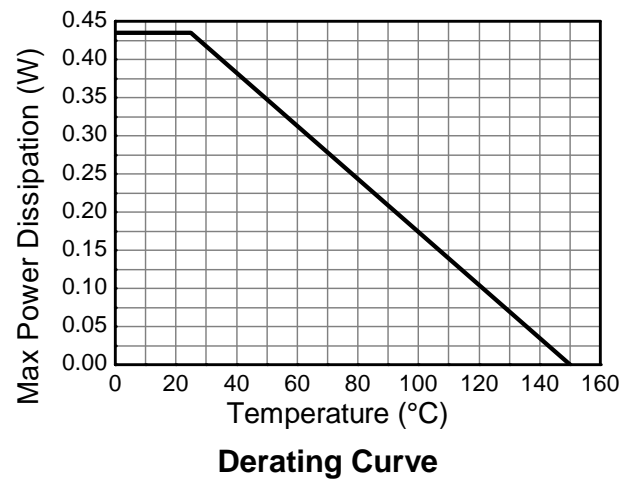
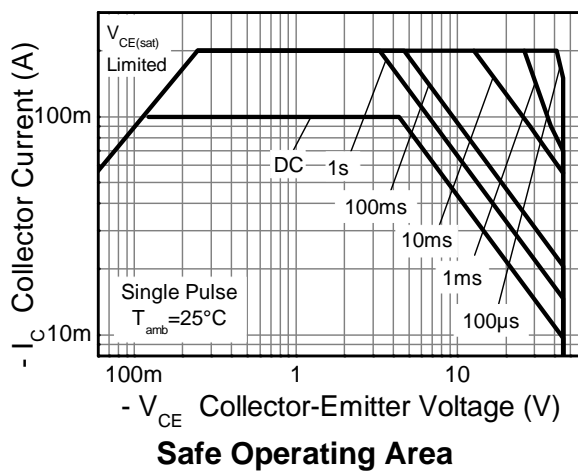
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	435	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	287	°C/W
Thermal Resistance, Junction to Lead (Note 6)	R <sub>θJL</sub>	150	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
- For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
  - Thermal resistance from junction to solder-point (on the exposed collector pad).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## Thermal Characteristics and Derating Information



**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typical	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	-100	—	V	I <sub>C</sub> = -50μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	-50	-90	—	V	I <sub>C</sub> = -50μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	-45	-65	—	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Collector-Base Breakdown Voltage	BV <sub>EBO</sub>	-6.0	-8.5	—	V	I <sub>E</sub> = -50μA, I <sub>C</sub> = 0
Collector-Base Cut-Off Current	I <sub>CBO</sub>	—	—	-15	nA	V <sub>CB</sub> = -40V
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	—	—	-15	nA	V <sub>CE</sub> = -40V
<b>ON CHARACTERISTICS</b> (Note 8)						
DC Current Gain	h <sub>FE</sub>	200	340 330	— 470	—	I <sub>C</sub> = -10μA, V <sub>CE</sub> = -5.0V I <sub>C</sub> = -2.0mA, V <sub>CE</sub> = -5.0V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	-70 -300	-175 -500	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	—	-760 -885	-1,000 -1,100	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage	V <sub>BE(on)</sub>	-600 —	-670 -715	-780 -850	mV	I <sub>C</sub> = -2.0mA, V <sub>CE</sub> = -5V I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5V
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	C <sub>obo</sub>	—	2.0	—	pF	V <sub>CB</sub> = -10.0V, f = 1.0MHz, I <sub>E</sub> = 0
Current Gain-Bandwidth Product	f <sub>T</sub>	100	340	—	MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f = 100MHz

Notes: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

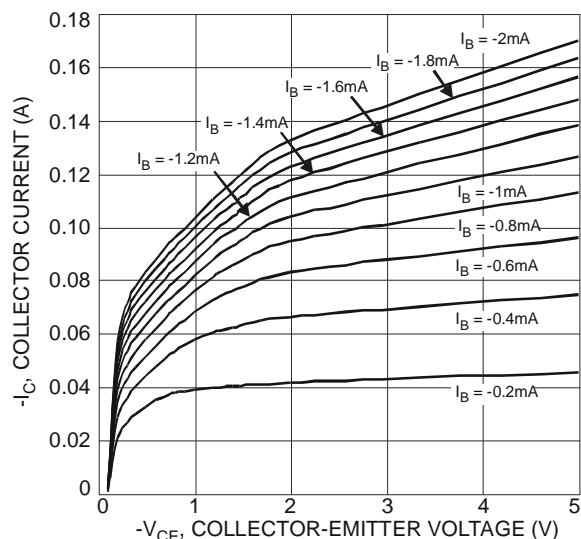


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

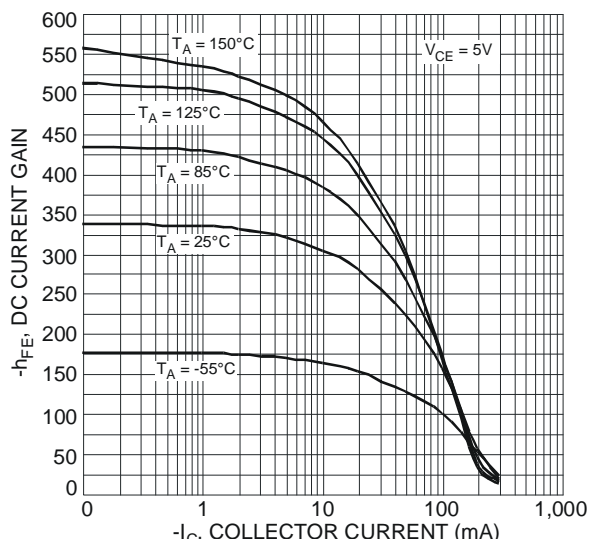


Fig. 5 Typical DC Current Gain vs. Collector Current

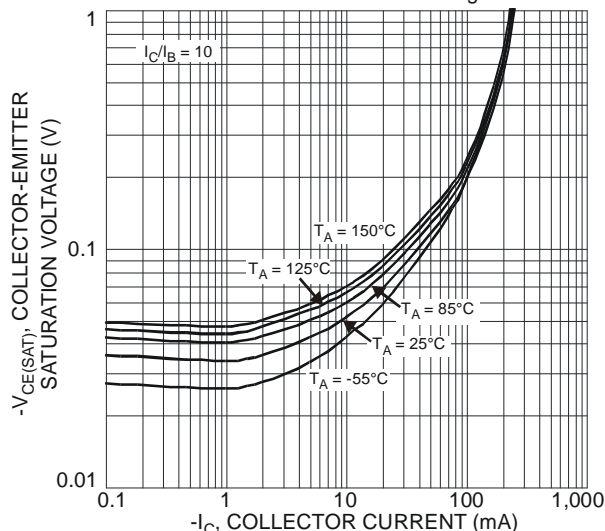


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

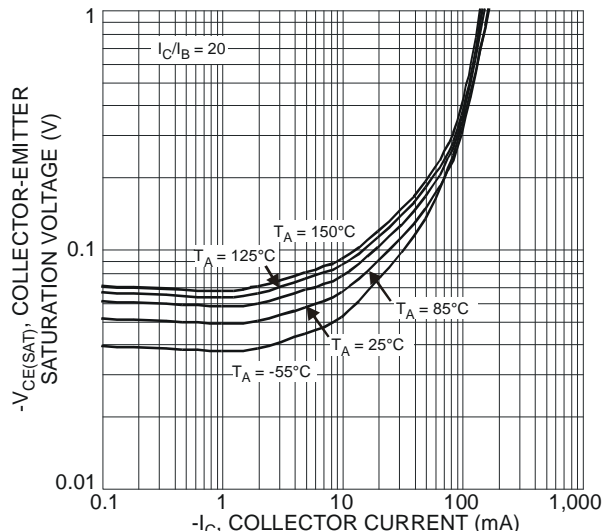


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

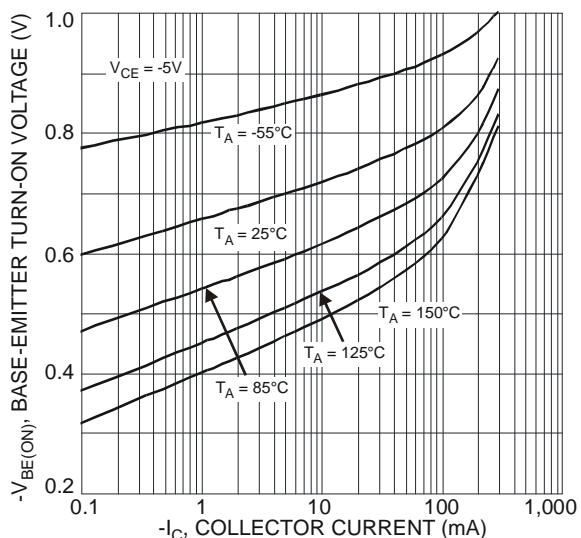


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

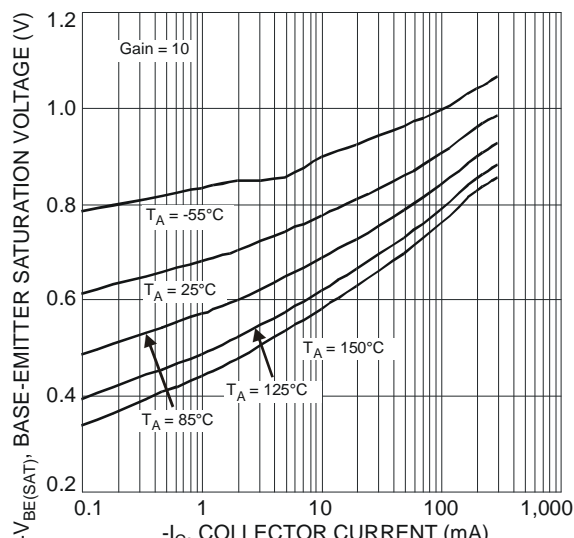
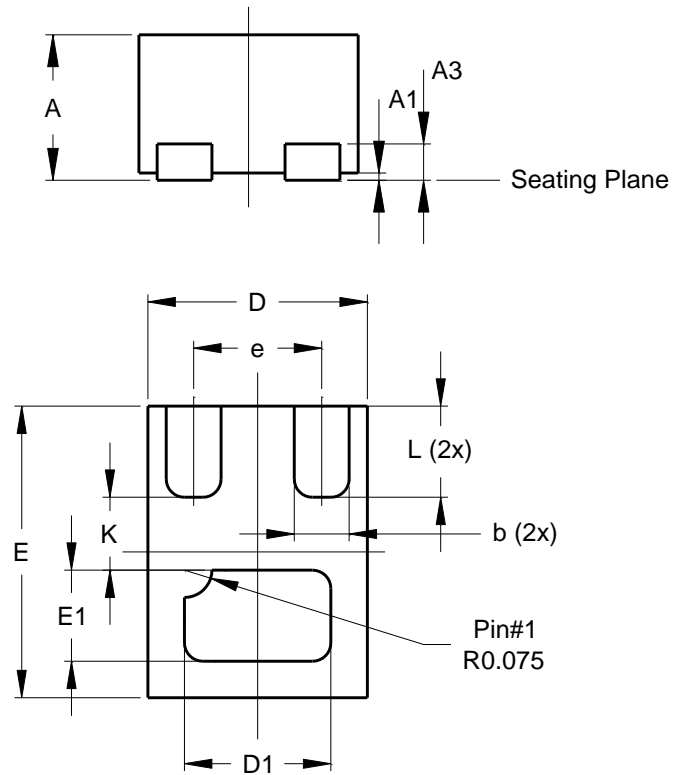


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

## Package Outline Dimensions

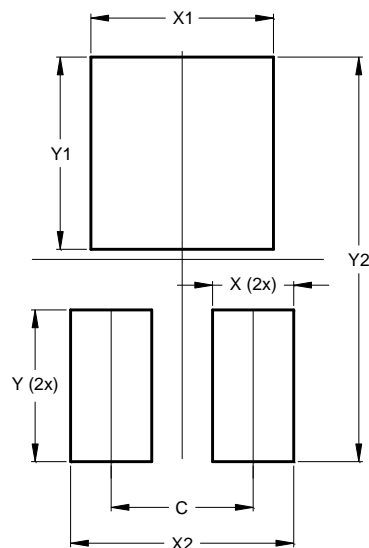
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



X2-DFN0806-3			
Dim	Min	Max	Typ
A	0.375	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.10
b	0.10	0.20	0.15
D	0.55	0.65	0.60
D1	0.35	0.45	0.40
E	0.75	0.85	0.80
E1	0.20	0.30	0.25
e	-	-	0.35
K	-	-	0.20
L	0.20	0.30	0.25
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.200
X1	0.450
X2	0.550
Y	0.375
Y1	0.475
Y2	1.000

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